# PROCESS FOR FORMING A SEMICONDUCTOR DEVICE

## Abstract of the Disclosure

A process for dry etching a passivation layer (42) of a semiconductor device is performed such that a low radio frequency (RF) power step is used when an underlying bond pad (22) is initially exposed and a high RF power step is used after the initial exposure. The process virtually eliminates or reduces the likelihood of bond pad (22) staining, particularly when a polyimide die coat layer (72) is subsequently formed over the semiconductor device (50).

Figure 9 accompanies this abstract.